



April 2000

QFET™

FQD1N50 / FQU1N50

500V N-Channel MOSFET

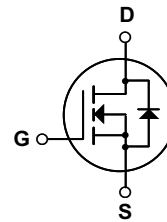
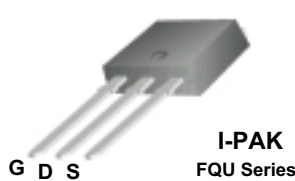
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.

Features

- 1.1A, 500V, $R_{DS(on)} = 9.0\Omega @ V_{GS} = 10V$
- Low gate charge (typical 4.0 nC)
- Low Crss (typical 3.0 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQD1N50 / FQU1N50	Units
V _{DSS}	Drain-Source Voltage	500	V
I _D	Drain Current - Continuous (T _C = 25°C)	1.1	A
	- Continuous (T _C = 100°C)	0.7	A
I _{DM}	Drain Current - Pulsed (Note 1)	4.4	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	80	mJ
I _{AR}	Avalanche Current (Note 1)	1.1	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *	2.5	W
	Power Dissipation (T _C = 25°C)	25	W
	- Derate above 25°C	0.2	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	5.0	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient *	--	50	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 400 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.55 A	--	6.8	9.0	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 0.55 A (Note 4)	--	0.98	--	S

Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	115	150	pF
C _{oss}	Output Capacitance		--	20	30	pF
C _{rss}	Reverse Transfer Capacitance		--	3.0	4.0	pF

Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 1.4 A, R _G = 25 Ω V _{DS} = 400 V, I _D = 1.4 A, V _{GS} = 10 V (Note 4, 5)	--	5	20	ns
t _r	Turn-On Rise Time		--	25	60	ns
t _{d(off)}	Turn-Off Delay Time		--	8	25	ns
t _f	Turn-Off Fall Time		--	20	50	ns
Q _g	Total Gate Charge		--	4.0	5.5	nC
Q _{gs}	Gate-Source Charge	--	1.1	--	nC	
Q _{gd}	Gate-Drain Charge	--	2.2	--	nC	

Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.1	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	4.4	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.1 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 1.4 A, di _F / dt = 100 A/μs (Note 4)	--	170	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.4	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 120mH, I_{AS} = 1.1A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 1.4A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

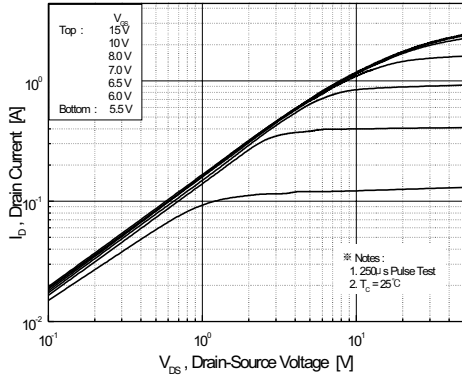


Figure 1. On-Region Characteristics

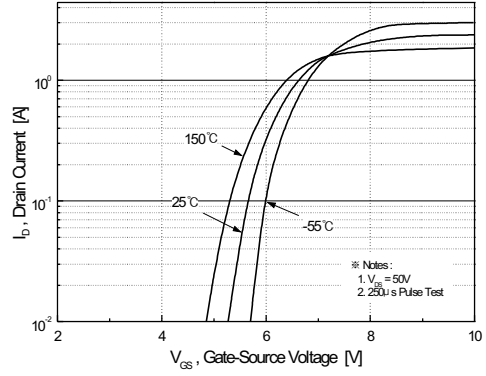


Figure 2. Transfer Characteristics

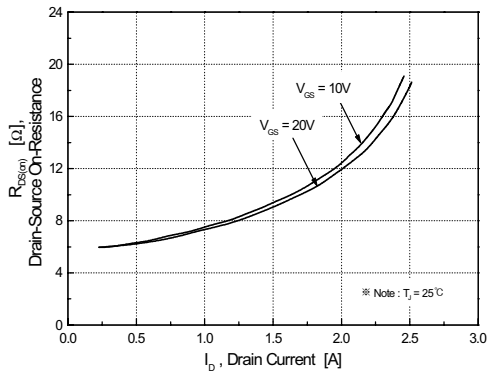


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

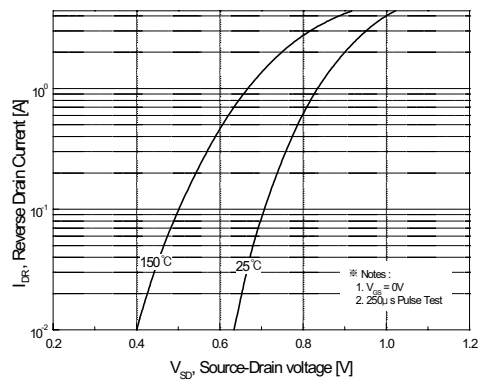


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

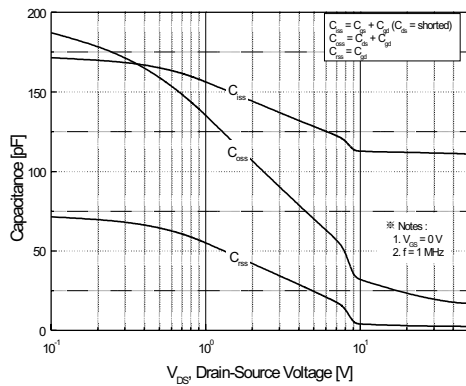


Figure 5. Capacitance Characteristics

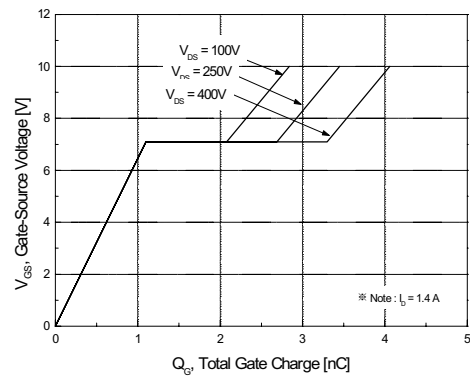


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

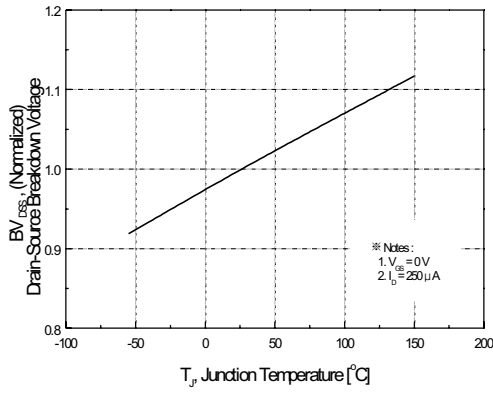


Figure 7. Breakdown Voltage Variation vs. Temperature

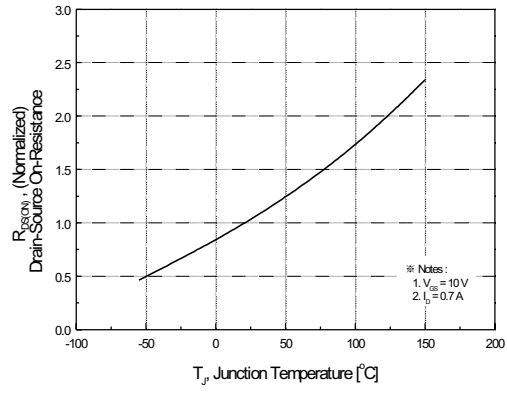


Figure 8. On-Resistance Variation vs. Temperature

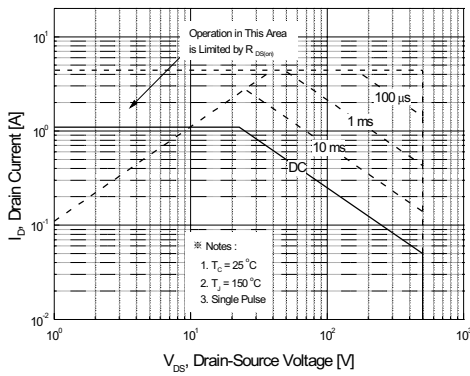


Figure 9. Maximum Safe Operating Area

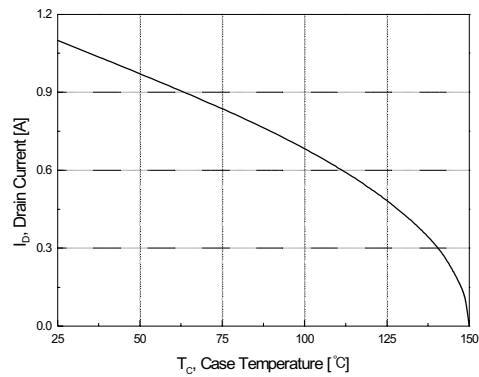


Figure 10. Maximum Drain Current vs. Case Temperature

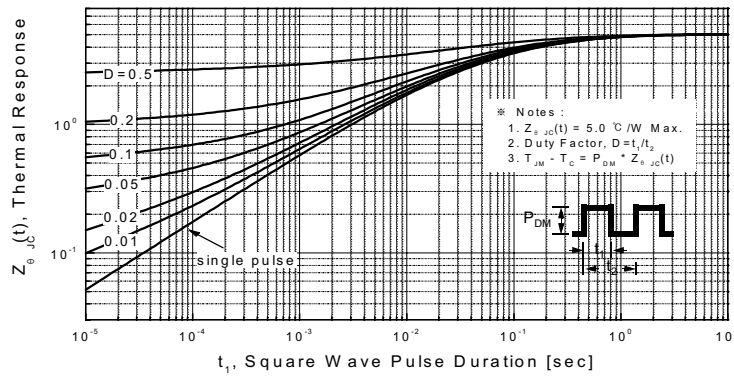
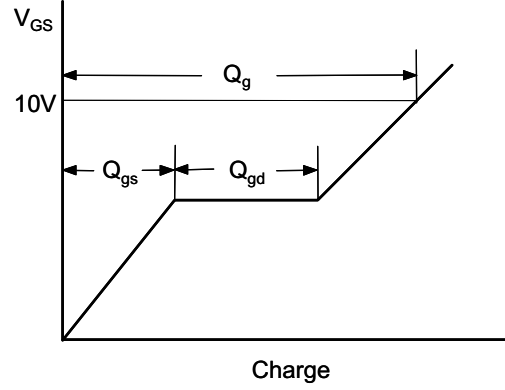


Figure 11. Transient Thermal Response Curve

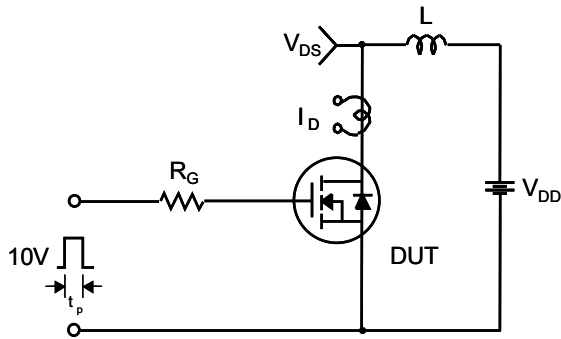
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

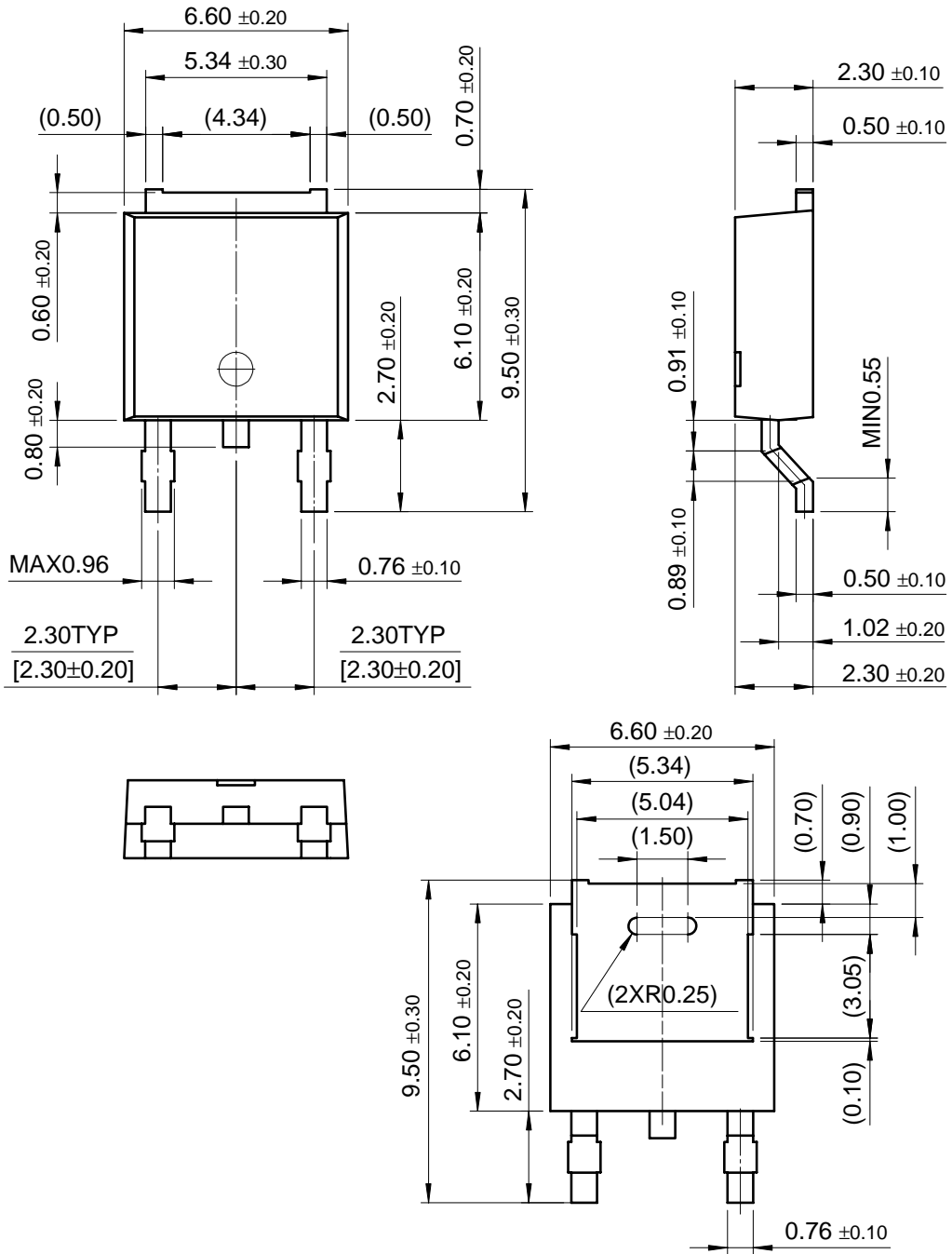


Peak Diode Recovery dv/dt Test Circuit & Waveforms



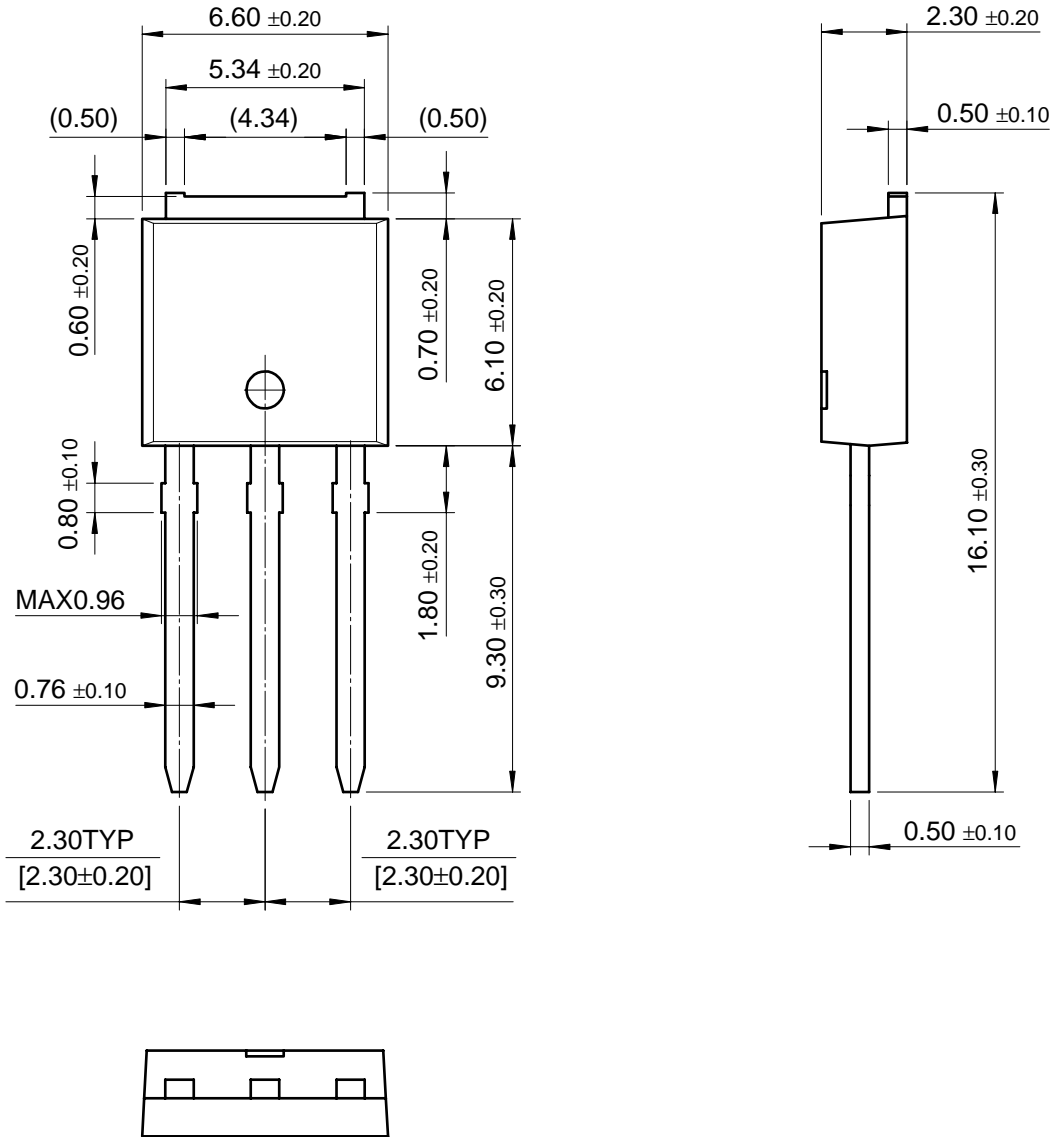
Package Dimensions

DPAK



Package Dimensions (Continued)

IPAK



FQD1N50 / FQU1N50

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE _x TM	HiSeC TM	SuperSOT TM -8
Bottomless TM	ISOPANAR TM	SyncFET TM
CoolFET TM	MICROWIRE TM	TinyLogic TM
CROSSVOLT TM	POP TM	UHC TM
E ² CMOS TM	PowerTrench [®]	VCX TM
FACT TM	QFET TM	
FACT Quiet Series TM	QS TM	
FAST [®]	Quiet Series TM	
FAST _r TM	SuperSOT TM -3	
GTO TM	SuperSOT TM -6	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Fairchild Semiconductor

SEARCH | Parametric | Cross Reference

space

Product Folders and

Applies

find products

Home >> Find products >>

Products groups

Analog and Mixed

Signal

Discrete

Interface

Logic

Microcontrollers

Non-Volatile

Memory

Optoelectronics

Markets and

applications

New products

Product selection and

parametric search

Cross-reference

search

technical information

buy products

technical support

my Fairchild

company

FQU1N50
500V N-Channel QFET

Contents

[General description](#) | [Features](#) | [Product status/pricing/packaging](#)

General description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.

[back to top](#)

Features

- 1.1A, 500V, $R_{DS(on)} = 9.0\Omega @ V_{GS} = 10V$
- Low gate charge (typical 4.0 nC)
- Low Crss (typical 3.0 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

[back to top](#)

Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
FQU1N50TU	Full Production	\$0.391	TO-251(IPAK)	3	RAIL

Datasheet

[Download this datasheet](#)

PDF

[e-mail this datasheet](#)

[E-]

This page [Print version](#)

Related Links

[Request samples](#)

[How to order products](#)

[Product Change Notices \(PCNs\)](#)

[Support](#)

[Distributor and field sales representatives](#)

[Quality and reliability](#)

[Design tools](#)

* 1,000 piece Budgetary Pricing

[back to top](#)

[Home](#) | [Find products](#) | [Technical information](#) | [Buy products](#) |
[Support](#) | [Company](#) | [Contact us](#) | [Site index](#) | [Privacy policy](#)

[© Copyright 2002 Fairchild Semiconductor](#)
